

Performance

- Frequency: 9.0-10.0GHz
- Gain: 7dB
- Output Power: 100W (Typ.)
- PAE: 37% (Typ.)
- Bias: 28V/-3V
- Hermetically Sealed Package
- Chip size: 24.0*17.4*4.4mm

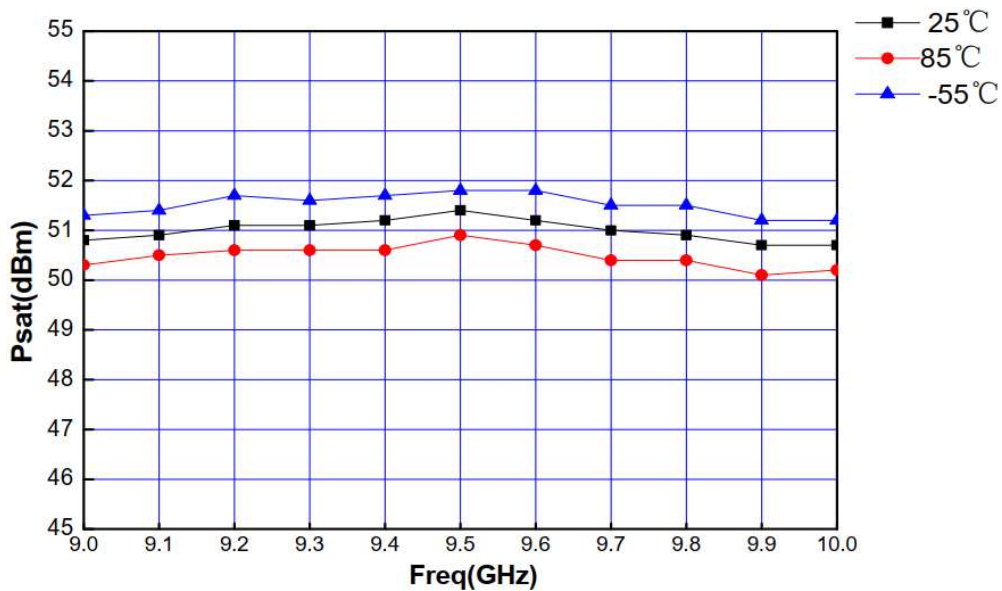


Electrical Specifications (Ta=+25°C, 50Ω system)

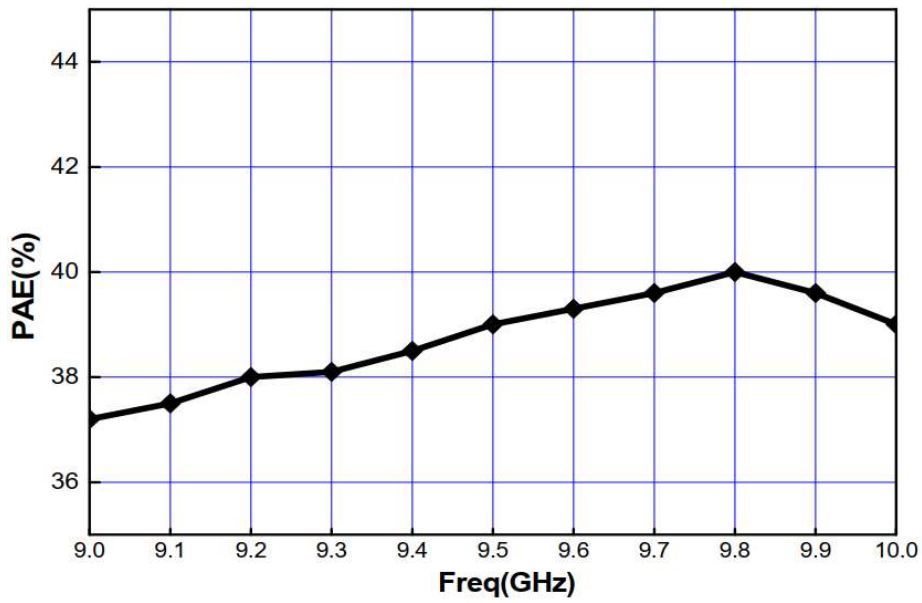
Symbol	Parameter	Test Condition	Min	Typical	Max	Unit
P _{out}	Output Power	V _d =28V, V _g =-3V Freq: 9.0-10.0GHz 100us, 10% D.C		50	-	dBm
G _p	Power Gain		-	7	-	dB
PAE	Power Added Efficiency		-	37	-	%
ΔG _p	Gain Flatness		-0.8	-	+0.8	dB

Test Curves (Ta=+25°C)

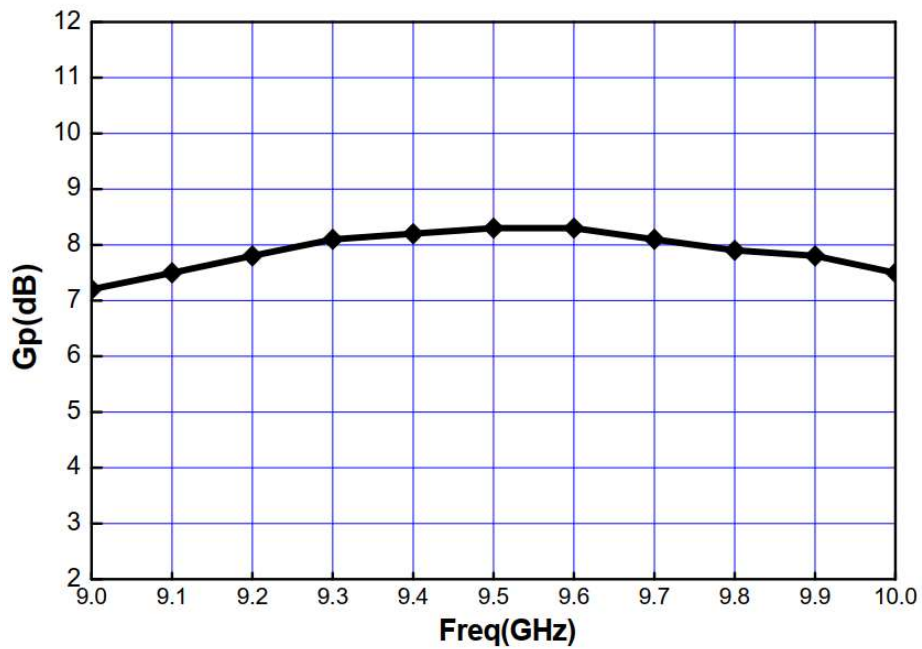
Output Power



Power Added Efficiency (PAE)



Gain

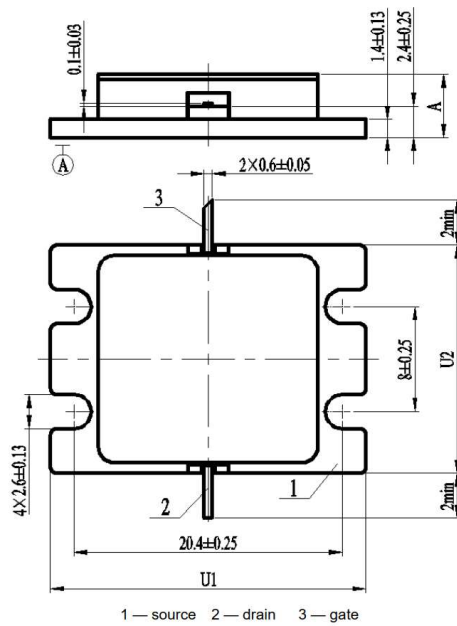


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vds	Drain Bias Voltage	32V	
Vgs	Gate Bias Voltage	-5V	
Tch	Channel Temperature	225°C	
Tstg	Storage Temperature	-55~175°C	

Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Symbol	Min	Max
U1	23.8	24.2
U2	17.2	17.6
A		5.2